NCE P-Channel Enhancement Mode Power MOSFET

Description

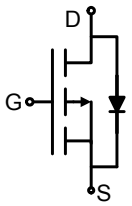
The FDMA905 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages .This device is suitable for use as a load switching application and a wide variety of other applications.

General Features

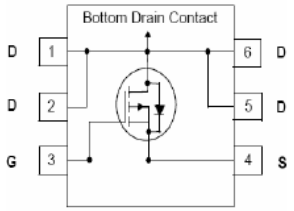
- V_{DS} = -12V,I_D = -6.7A
  $R_{DS(ON)}$ < 27mΩ @ V_{GS}=-2.5V
  $R_{DS(ON)}$ < 21mΩ @ V_{GS}=-4.5V
- Advanced trench MOSFET process technology
- Ultra low on-resistance with low gate charge

Application

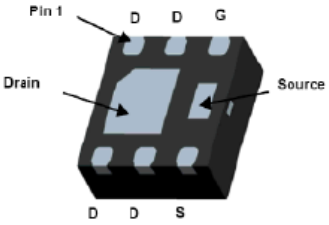
- PWM applications
- Load switch
- Battery charge in cellular handset



Schematic diagram



Pin assignment



DFN2X2-6L bottom view

Package marking and ordering information

Device Marking	Device	Device Package	Reel Size	Tape Width	Quantity
905T	FDMA905	DFN2X2-6L	-	-	-

Absolute maximum ratings (TA=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-12	V
Gate-Source Voltage	V_{GS}	±8	V
Drain Current-Continuous	I_D	-6.7	A
Drain Current -Pulsed (Note 1)	I_{DM}	-65	A
Maximum Power Dissipation	P_D	2.5	W
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Ambient (Note 2)	$R_{\theta JA}$	50	℃/W
Thermal Resistance,Junction-to-Case (Note 2)	$R_{\theta JC}$	6.9	℃/W

Electrical characteristics (TA=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)\ DSS}$	V_{GS}=0V I_D=-250μA	-12	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-12V,V_{GS}=0V	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±8V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250μA	-0.4	-0.7	-1	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-4.5V, I_D=-6.7A	-	17	21	mΩ
		V_{GS}=-2.5V, I_D=-6.2A	-	21	27	mΩ
Forward Transconductance	g_{FS}	V_{DS}=-10V,I_D=-6.7A	-	40	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=-10V,V_{GS}=0V, F=1.0MHz	-	2700	-	PF
Output Capacitance	C_{oss}		-	680	-	PF
Reverse Transfer Capacitance	C_{rss}		-	590	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=-10V,I_D=-1A V_{GS}=-4.5V,R_{GEN}=10Ω	-	11	-	nS
Turn-on Rise Time	t_r		-	35	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	30	-	nS
Turn-Off Fall Time	t_f		-	10	-	nS
Total Gate Charge	Q_g	V_{DS}=-6V,I_D=-10A, V_{GS}=-4.5V	-	35	48	nC
Gate-Source Charge	Q_{gs}		-	5	-	nC
Gate-Drain Charge	Q_{gd}		-	10	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=-8A	-	-	-1.2	V
Diode Forward Current (Note 2)	I_S		-	-	-16	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

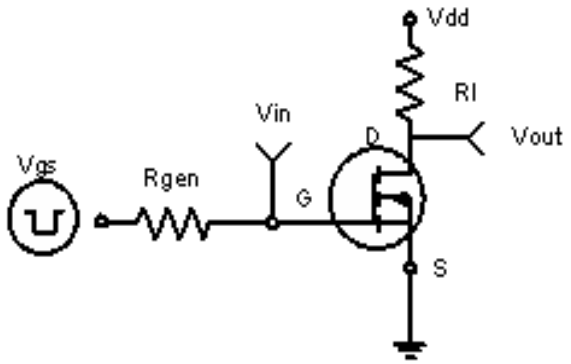


Figure 1:Switching Test Circuit

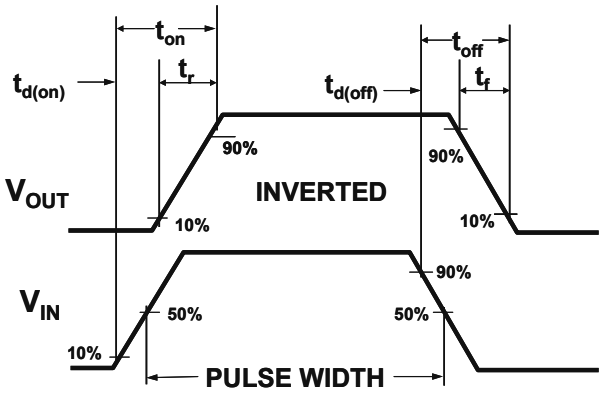
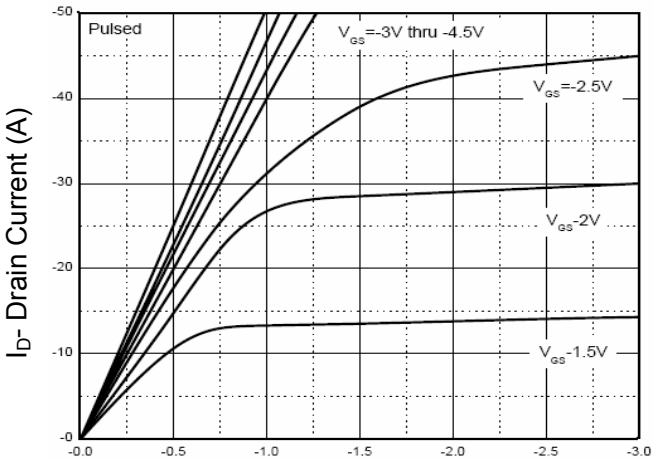
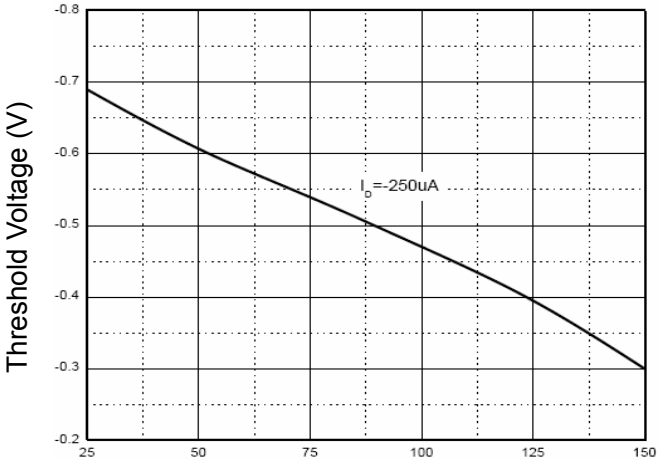


Figure 2:Switching Waveforms



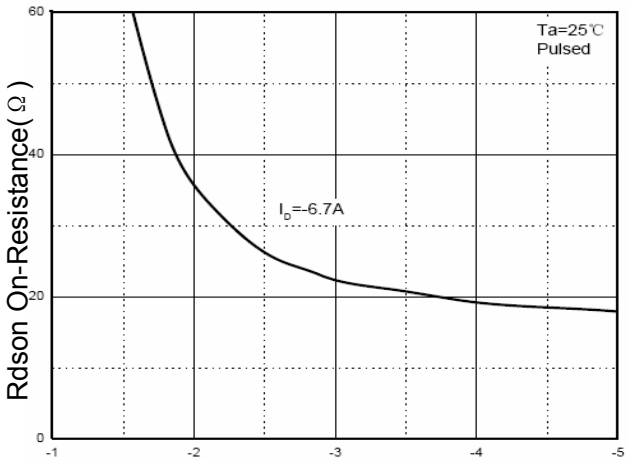
Vds Drain-Source Voltage (V)

Figure 3 Output Characteristics



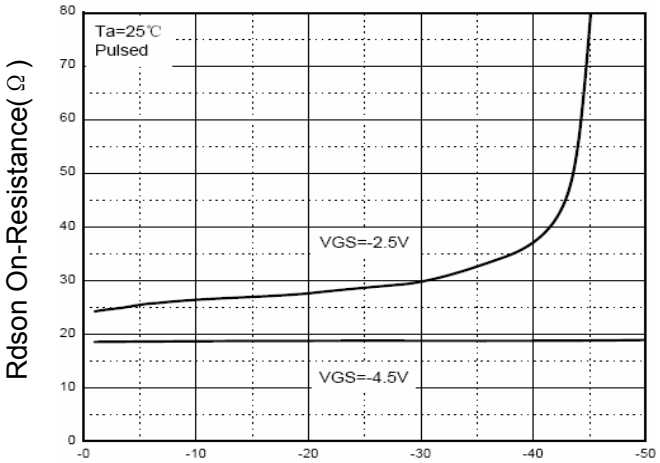
TJ-Junction Temperature(℃)

Figure 4 Drain Current



Vgs Gate-Source Voltage (V)

Figure 5 Rdson vs Vgs



ID- Drain Current (A)

Figure 6 Drain-Source On-Resistance

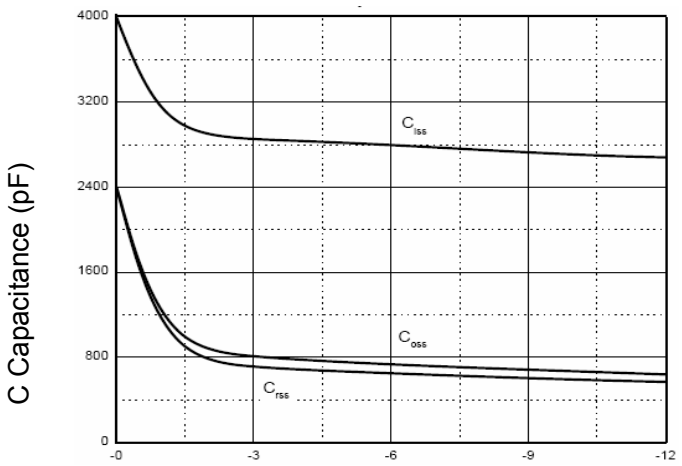


Figure 7 Capacitance vs Vds

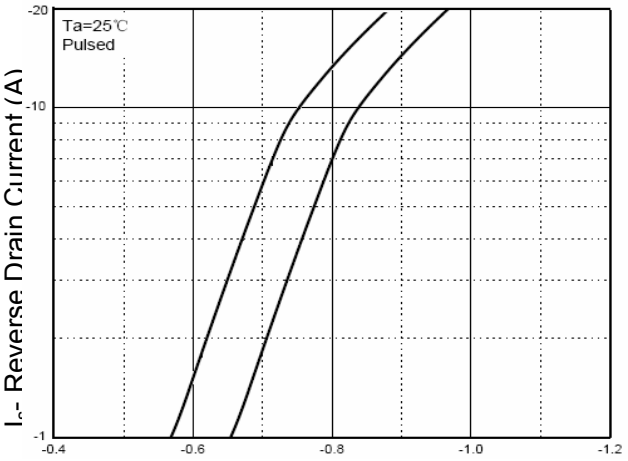
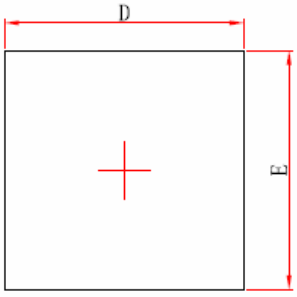
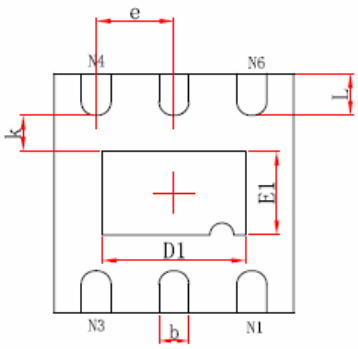


Figure 8 Source- Drain Diode Forward

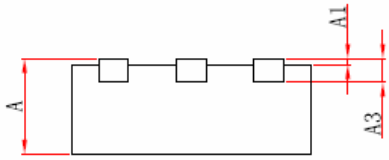
DFN2X2-6L Package Information



Top VIew



Bottom View



Side View

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700/0.800	0.800/0.900	0.028/0.031	0.031/0.035
A1	0.000	0.050	0.000	0.002
A3	0.203REF.		0.008REF.	
D	1.900	2.100	0.075	0.083
E	1.900	2.100	0.075	0.083
D1	1.100	1.300	0.043	0.051
E1	0.600	0.800	0.024	0.031
k	0.200MIN.		0.008MIN.	
b	0.180	0.300	0.007	0.012
e	0.650TYP.		0.026TYP.	
L	0.250	0.450	0.010	0.018

NOTES

1. All dimensions are in millimeters.
2. Tolerance ±0.10mm (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.